

## PRODUCT / PROCESS CHANGE NOTIFICATION

### 1. PCN basic data

1.1 Company	 STMicroelectronics International N.V
1.2 PCN No.	MICROCONTROLLERS/24/14731
1.3 Title of PCN	ASE KaoHsiung (Taiwan) LQFP24x24 package copper palladium bonding wire introduction on STM32H56x and STM32H57x on additional listed products.
1.4 Product Category	STM32H56x, STM32H57x
1.5 Issue date	2024-07-10

### 2. PCN Team

2.1 Contact supplier	
2.1.1 Name	ROBERTSON HEATHER
2.1.2 Phone	+1 8475853058
2.1.3 Email	heather.robertson@st.com
2.2 Change responsibility	
2.2.1 Product Manager	Ricardo Antonio DE SA EARP
2.1.2 Marketing Manager	Veronique BARLATIER
2.1.3 Quality Manager	Pascal NARCHE

### 3. Change

3.1 Category	3.2 Type of change	3.3 Manufacturing Location
Materials	Direct Material: Bond Wire - Metallurgy (metallic composition/ raw material)	ASE Kaohsiung (TAIWAN)

### 4. Description of change

	Old	New
4.1 Description	Current Wire bonding material: - ASE KaoHsiung (Taiwan) gold wire	New Wire bonding material : - ASE KaoHsiung (Taiwan) copper palladium wire
4.2 Anticipated Impact on form, fit, function, quality, reliability or processability?	no impact on form, Fit, Function	

### 5. Reason / motivation for change

5.1 Motivation	To improve service
5.2 Customer Benefit	SERVICE IMPROVEMENT

### 6. Marking of parts / traceability of change

6.1 Description	traceability ensured by ST Internal tools
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### 7. Timing / schedule

7.1 Date of qualification results	2024-07-04
7.2 Intended start of delivery	2024-07-10
7.3 Qualification sample available?	Upon Request

### 8. Qualification / Validation

8.1 Description	14731 MDG-GPM- RER2303-V2.0-PCN13840-PCN14731-ASEKH LQ24x24 Low cost wire introduction.pdf		
8.2 Qualification report and qualification results	Available (see attachment)	Issue Date	2024-07-10

### 9. Attachments (additional documentations)

10. Affected parts		
10.1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
	STM32H563IGT6	
	STM32H563IIT3Q	
	STM32H563IIT6	
	STM32H573IIT3Q	
	STM32H573IIT6	

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## Reliability Evaluation Report

### MDG-GPM-RER2303

ASEKH LQFP24x24 Low cost wire introduction  
(PCN13840-PCN14731)

General Information	
Commercial Product	STM32F427IIT6, STM32H725IGT6 STM32F745IET7, STM32F217ZGT6, STM32H573IIT6
Product Line	419X66, 483X66, 449X66, 411X66, 484X66
Die revision	419 cut 2.2, 483 cut 1.1 449 cut 1.1, 411 cut 2.4, 484 cut 1.3
Product Description	STM32F4xx, STM32H7xx STM32F7xx, STM32F2xx, STM32H5xx
Package	LQFP 176 24x24x1.4
Silicon Technology	CMOSM40, CMOSM10
Division	MDG-GPM

Traceability	
Diffusion Plant	Crolles 300 TSMC Fab14 DIFF
Assembly Plant	SC ASE - TAIWAN

Reliability Assessment	
Pass	X
Fail	

Release	Date	Author	Function
1.0	02/06/2023	Gabin BOSCO	GPM BE Q&R
2.0	19/06/2024	Celine Navarro	GPM BE Q&R

#### Approved by:

Rev 1.0

Name	Function	Location	Date
Berengere ROUTIER-SCAPPUCCI	GPM BE Q&R Manager	ROUSSET	02/06/2023
Pascal NARCHE	Subgroup Quality Manager	ROUSSET	02/06/2023

Rev2.0

Name	Function	Location	Date
Berengere ROUTIER-SCAPPUCCI	GPM BE Q&R Manager	ROUSSET	03/07/2024

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## RELIABILITY EVALUATION OVERVIEW

- **OBJECTIVE**

The aim of this report is to present the reliability evaluation performed for the qualification of ASEKH (Taiwan) LQFP24x24 with copper-palladium wires on M10 and M40 technos.

PCN13840 changes are described here below:

	Existing back-end line		Added back-end line		
Assembly site	ASE KaoHsiung (Taiwan)				
Wire	Gold 0.8mil		CuPdAu 0.8mil		
GLUE	Sumitomo CRM 1076WA	YIZTECH 8143	Sumitomo CRM 1076WA	YIZTECH 8143	HITACHI EN4900G
Marking composition	Without 2D		With 2D Marking		

PCN14731 changes are described here below:

	Existing back-end line		Added back-end line	
Assembly site	ASE KaoHsiung (Taiwan)			
Wire	Gold 0.8mil		CuPdAu 0.8mil	
GLUE	SUMITOMO CRM 1076WA		HITACHI EN4900G	
Marking composition	Without 2D		With 2D Marking	

- CONCLUSION

All reliability tests have been completed with positive results. Neither functional nor parametric rejects were detected at final electrical testing.

Package oriented tests have not put in evidence any criticality. Physical analysis performed on samples submitted to tests has not put in evidence any issue. ESD CDM are in accordance with ST spec.

Based on the overall results obtained, products below have positively passed reliability evaluation:

Line code	Commercial product	Diff plant	Assy plant
419X66	STM32F427IIT6	TSMC Crolles	ASEKH (TAIWAN)
483X66	STM32H725IGT6		
449x66	STM32F745IET7		
411X66	STM32F217ZGT6		
484X66	STM32H573IIT6		

According to good reliability tests results in line with validated product mission profile and reliability strategy, the qualification is granted for all Finished Goods diffused in TSMC M10 and Crolles M10/M40, assembled in LQFP24x24 at ASEKH (Taiwan) in copper-palladium wires.

Refer to Section 3.0 for reliability test results.

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## 1. RELIABILITY STRATEGY

Reliability trials performed as part of this reliability evaluation are in agreement with ST 0061692 specification, in full compliancy with the JESD-47 international standard.

For details on test conditions, generic data used and specifications references, refer to test results summary in section 3.

## 2. PRODUCT OR TEST VEHICLE CHARACTERISTICS

### 2.1. Generalities

Package line	Device (Partial RawLine Code)	Diffusion process	Number of lots
LQFP 24x24x1.4 176L	1T*419	CMOSM10 TSMC	1
	1T*483	CMOSM40 Crolles	1
	1T*449	CMOSM10 Crolles	1
	1T*411	CMOSM10 Crolles	1
	1T*484	CMOSM40 Crolles	1

## 2.2. Traceability

### 2.2.1. Wafer Fab Information

Die 419 - LQFP24x24

Wafer Fab Information			
FAB1			
Wafer fab name / location	TSMC Taiwan / TSMC Fab14 DIFF		
Wafer diameter	12 inches		
Wafer thickness	775±25 µm		
Silicon process technology	CMOSM10		
Number of masks	44		
Die finishing front side (passivation) materials/Thickness	USG+NITRIDE/1,1µm		
Die finishing back side Materials	RAW SILICON		
Die area (Stepping die size)	25.43 mm <sup>2</sup> (5582, 4556)		
Die pad size	Geometry	Open(X,Y)	
	Rectangular	59,123 µm	
Sawing street width (X,Y)	80,80 µm		
Metal levels/Materials/Thicknesses	Wire bond pad metal	Composition	Thickness
	1	TaN/Ta/CuSeed/Cu	0.22 µm
	2	TaN/Ta/CuSeed/Cu	0.28 µm
	3	TaN/Ta/CuSeed/Cu	0.28 µm
	4	TaN/Ta/CuSeed/Cu	0.28 µm
	5	TaN/Ta/CuSeed/Cu	0.28 µm
	6	Ta/TaN/AlCu	0.73 µm
	7	AlCu	1.2 µm

## Die 483 - LQFP24x24

Wafer Fab Information																													
FAB1																													
Wafer fab name / location	Crolles 300 / Crolles 300 12																												
Wafer diameter	12 inches																												
Wafer thickness	775±25 µm																												
Silicon process technology	CMOSM40																												
Number of masks	51																												
Die finishing front side (passivation) materials/Thickness	PSG+NITRIDE/1,1µm																												
Die finishing back side Materials	RAW SILICON																												
Die area (Stepping die size)	15.66 mm <sup>2</sup> (3753, 4175)																												
Die pad size	<table border="1"> <thead> <tr> <th>Geometry</th><th>Open(X,Y)</th></tr> </thead> <tbody> <tr> <td>Rectangular</td><td>54.9,54.4 µm</td></tr> </tbody> </table>	Geometry	Open(X,Y)	Rectangular	54.9,54.4 µm																								
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Rectangular	54.9,54.4 µm																												
Sawing street width (X,Y)	80,80 µm																												
Metal levels/Materials/Thicknesses	<table border="1"> <thead> <tr> <th>Wire bond pad metal</th><th>Composition</th><th>Thickness</th></tr> </thead> <tbody> <tr> <td>1</td><td>Cu</td><td>0.11 µm</td></tr> <tr> <td>2</td><td>Cu</td><td>0.14 µm</td></tr> <tr> <td>3</td><td>Cu</td><td>0.14 µm</td></tr> <tr> <td>4</td><td>Cu</td><td>0.14 µm</td></tr> <tr> <td>5</td><td>Cu</td><td>0.14 µm</td></tr> <tr> <td>6</td><td>Cu</td><td>0.86 µm</td></tr> <tr> <td>7</td><td>Cu</td><td>0.86 µm</td></tr> <tr> <td>8</td><td>Ta/TaN/AlCu</td><td>1.525 µm</td></tr> </tbody> </table>		Wire bond pad metal	Composition	Thickness	1	Cu	0.11 µm	2	Cu	0.14 µm	3	Cu	0.14 µm	4	Cu	0.14 µm	5	Cu	0.14 µm	6	Cu	0.86 µm	7	Cu	0.86 µm	8	Ta/TaN/AlCu	1.525 µm
Wire bond pad metal	Composition	Thickness																											
1	Cu	0.11 µm																											
2	Cu	0.14 µm																											
3	Cu	0.14 µm																											
4	Cu	0.14 µm																											
5	Cu	0.14 µm																											
6	Cu	0.86 µm																											
7	Cu	0.86 µm																											
8	Ta/TaN/AlCu	1.525 µm																											

**Die 449 – LQFP24x24**

Wafer Fab Information			
FAB1			
Wafer fab name / location	Crolles 300 / Crolles 300 12		
Wafer diameter (inches)	12		
Wafer thickness (µm)	775		
Silicon process technology	CMOSM10		
Number of masks	42		
Die finishing front side (passivation) materials	PSG NITRIDE		
Die finishing back side Materials	RAW SILICON		
Die area (Stepping die size)	26.913416 mm <sup>2</sup> (5884, 4574)		
Die pad size	Geometry	Open(X,Y)	
	Rectangular	59,123 µm	
Sawing street width (X,Y) (µm)	80,80		
Metal levels/Materials/Thicknesses	Wire bond pad metal	Composition	Thickness
	1	TaN/CuSeed/Cu	0.24 µm
	2	TaN/CuSeed/Cu	0.33 µm
	3	TaN/CuSeed/Cu	0.33 µm
	4	TaN/CuSeed/Cu	0.33 µm
	5	TaN/CuSeed/Cu	0.33 µm
	6	TaN/CuSeed/Cu	0.85 µm
	7	AlCu/TinArc	1.45 µm

## Die 411 – LQFP 24x24

Wafer Fab Information			
FAB1			
Wafer fab name / location	Crolles 300 / Crolles 300 12		
Wafer diameter	12 inches		
Wafer thickness	775±25 µm		
Silicon process technology	CMOSM10		
Number of masks	42		
Die finishing front side (passivation) materials/Thickness	PSG+NITRIDE/1.1µm		
Die finishing back side Materials	RAW SILICON		
Die area (Stepping die size)	14.71 mm <sup>2</sup> (4006, 3674)		
Die pad size	Geometry	Open(X,Y)	
	Rectangular	59,123 µm	
Sawing street width (X,Y)	Rectangular	63,73 µm	
	80,80 µm		
Metal levels/Materials/Thicknesses	Wire bond pad metal	Composition	Thickness
	1	TaN/CuSeed/Cu	0.24 µm
	2	TaN/CuSeed/Cu	0.33 µm
	3	TaN/CuSeed/Cu	0.33 µm
	4	TaN/CuSeed/Cu	0.33 µm
	5	TaN/CuSeed/Cu	0.33 µm
	6	TaN/CuSeed/Cu	0.85 µm
	7	AlCu/TinArc	1.45 µm

## Die 484 – LQFP 24x24

Wafer Fab Information			
FAB1			
Wafer fab name / location	Crolles 300 / Crolles 300 12		
Wafer diameter	12 inches		
Wafer thickness	775±25 µm		
Silicon process technology	CMOSM40		
Number of masks	51		
Die finishing front side (passivation) materials/Thickness	PSG+NITRIDE/1.1µm		
Die finishing back side Materials	RAW SILICON		
Die area (Stepping die size)	11.5988 mm <sup>2</sup> (3518, 3297)		
Die pad size	54.9,54.9 µm		
Sawing street width (X,Y)	80,80 µm		
Metal levels/Materials/Thicknesses	Wire bond pad metal	Composition	Thickness
	1	TaN/Ta/CuSeed/Cu	0.110 µm
	2	TaN/Ta/CuSeed/Cu	0.140 µm
	3	TaN/Ta/CuSeed/Cu	0.140 µm
	4	TaN/Ta/CuSeed/Cu	0.140 µm
	5	TaN/Ta/CuSeed/Cu	0.140 µm
	6	TaN/Ta/CuSeed/Cu	0.850 µm
	7	TaN/Ta/CuSeed/Cu	0.850 µm
	8	Ta/TaN/AiCu	1.525 µm

### 2.2.2. Assembly Information

Package: LQFP 176 24x24x1.4	483	449	411 & 419	484		
Assembly plant name / location	ASE TAIWAN / SC ASE - TAIWAN					
Pitch	0.4mm		0.5mm			
Die thickness after back-grinding	375+/-25µm	300+/-25µm		375+/-25µm		
Die sawing method	Laser groove + mechanical sawing					
<b>Bill of Material elements</b>						
Lead frame/Substrate material/ reference	LF# A25472-0 LQ176L DR Pure tin C7025 SLOT PWB 6sq	LF# A19506-0 FOR LQ 176L WITH SLOT 243 sq				
Lead frame finishing (material/thickness)	Pure Tin (e3): Tolerance 7 to 20µm					
Die attach material/type(glue)/supplier	GLUE SUMITOMO EPOXY CRM 1076WA	HITACHI EN4900G	GLUE YIZTECH 8143	HITACHI EN4900G		
Wire bonding material/diameter	Copper-palladium 0.8 mils					
Molding compound material/supplier/reference	MOLDING RESIN SUMITOMO EME-G631SH		MOLDING RESIN SUMITOMO EME-G631H	MOLDING RESIN SUMITOMO EME-G631SH		
Package Moisture Sensitivity Level (JEDEC J-STD020D)	3					

### 2.2.3. Reliability testing information

Reliability Testing Information	
Reliability laboratory name / location	Grenoble Rel Lab, Rousset MDG Rel Lab, Shenzhen BE Lab ASE Rel lab, Muar BE Lab

Note: ST is ISO 9001 certified. This induces certification of all internal and subcontractor labs. ST certification document can be downloaded under the following link: [http://www.st.com/content/st\\_com/en/support/quality-and-reliability/certifications.html](http://www.st.com/content/st_com/en/support/quality-and-reliability/certifications.html)

### 3. TEST RESULTS SUMMARY

#### 3.1. Lot information

Lot #	Diffusion Lot	Die Revision (Cut)	Trace Code	Raw Line	Package	Note
Lot 1	9R124619	419 cut 2.2	AA140007	201T*419CSX5	LQFP 176 24x24x1.4	1 Reliability lot
Lot 2	VQ046607	483 cut 1.1	AA137095	201T*483CSXZ		1 Reliability lot
Lot 3	VQ205526	449 cut 1.1	AA228001	2A1T*449QCXZ		1 Reliability lot
Lot 4	VQ111287	411 cut 2.4	AA140008	201T*411CSX2		1 Reliability lot
Lot 5	VQ316550	484 cut 1.2	AA351005	211T*484QCXX		1 Reliability lot

#### 3.2. Test plan and results summary

#### ACCELERATED ENVIRONMENT STRESS TESTS

Test code	Stress method	Stress Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
PC	JSTD 020 JESD 22-A113 7191395	24h bake@125°C, MSL3 (192h/30°C/60%RH) 3x Reflow simulation Peak Reflow Temp= 260°C	5	308	1540	Lot 1: 0/308 Lot 2: 0/308 Lot 3: 0/308 Lot 4: 0/308 Lot 5: 0/308	NA
HTSL	JESD22-A103	Ta= 150°C Duration= 1000hrs <input checked="" type="checkbox"/> After PC	5	77	385	Lot 1: 0/77 Lot 2: 0/77 Lot 3: 0/77 Lot 4: 0/77 Lot 5: 0/77	NA
TC	JESD22-A104	Ta= -65/150°C Cyc= 500 <input checked="" type="checkbox"/> After PC	5	77	385	Lot 1: 0/77 Lot 2: 0/77 Lot 3: 0/77 Lot 4: 0/77 Lot 5: 0/77	NA
THB	JESD22-A101	Ta=85°C/85%RH VDD=3v6 Duration= 1000hrs <input checked="" type="checkbox"/> After PC	5	77	385	Lot 1: 0/77 Lot 2: 0/77 Lot 3: 0/77 Lot 4: 0/77 Lot 5: 0/77	NA
UHAST	JESD22-A118	Ta=130°C ,85% RH, 2 Atm Duration= 96hrs <input checked="" type="checkbox"/> After PC	5	77	385	Lot 1: 0/77 Lot 2: 0/77 Lot 3: 0/77 Lot 4: 0/77 Lot 5: 0/77	NA

**ELECTRICAL TEST VERIFICATION**

Test code	Stress method	Stress Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
CDM	JEDEC JS-002	Voltage=500V for 411/484 Voltage=250V for 449/419/483	5	3	15	Lot 1: 0/3 Lot 2: 0/3 Lot 3: 0/3 Lot 4: 0/3 Lot 5: 0/3	NA

**PACKAGE ASSEMBLY INTEGRITY TESTS**

Test code	Stress method	Stress Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
CA	Construction analysis including -Wire bond shear -Wire bond pull	ST internal specifications	5	50	250	Lot 1: 0/50 Lot 2: 0/50 Lot 3: 0/50 Lot 4: 0/50 Lot 5: 0/50	NA

Note: Test method revision reference is the one active at the date of reliability trial execution.

**4. APPLICABLE AND REFERENCE DOCUMENTS**

Reference	Short description
JESD47	Stress-Test-Driven Qualification of Integrated Circuits
SOP2.4.4	Record Management Procedure
SOP2.6.2	Internal Change Management
SOP2.6.7	Finished Good Maturity Management
SOP2.6.9	Package & Process Maturity Management in BE
SOP2.6.11	Program Management for Product Development
SOP2.6.17	Management of Manufacturing Transfers
SOP2.6.19	Front-End Technology Platform Development and Qualification
DMS 0061692	Reliability Tests and Criteria for Product Qualification
JEDEC JS-002	Electrostatic discharge (ESD) sensitivity testing charge device model (CDM)
JESD 22-A103	High Temperature Storage Life
J-STD-020	Moisture/reflow sensitivity classification for non-hermetic solid state surface mount devices
JESD22-A113	Preconditioning of non-hermetic surface mount devices prior to reliability testing
JESD22-A118	Unbiased Highly Accelerated temperature & humidity Stress Test
JESD22-A104	Temperature cycling
JESD22-A101	Temperature Humidity Bias

## 5. GLOSSARY

<b>ESD - CDM</b>	Electrostatic Discharge - Charged device model
<b>CA</b>	Construction analysis
<b>HTSL</b>	Storage Life High temperature storage life
<b>PC</b>	Preconditioning
<b>TC</b>	Temperature Cycling
<b>THB</b>	Temperature Humidity Bias
<b>UHAST</b>	Unbiased HAST (Highly Accelerated Stress Test)
<b>DMS</b>	ST Advanced Documentation Controlled system/ Documentation Management system

## 6. REVISION HISTORY

<b>Release</b>	<b>Date</b>	<b>Description</b>
1.0	02/02/2023	Initial release
2.0	18/06/2024	Added die 484

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**PRODUCT/PROCESS  
CHANGE NOTIFICATION  
PCN14731 – Additional information**

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**ASE KaoHsiung (Taiwan) LQFP24x24 package copper palladium bonding wire introduction on STM32H56x and STM32H57x on additional listed products.**

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**MRDF – General Purpose Microcontrollers Division (GPM)**

**What are the changes?**

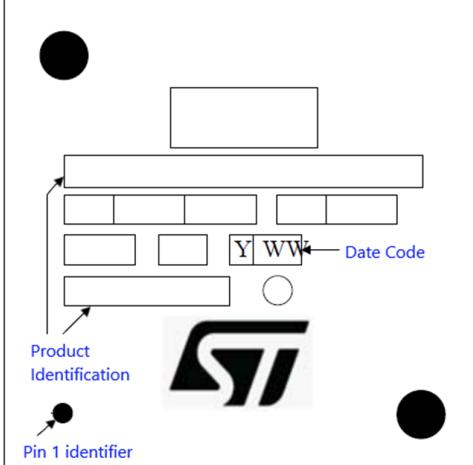
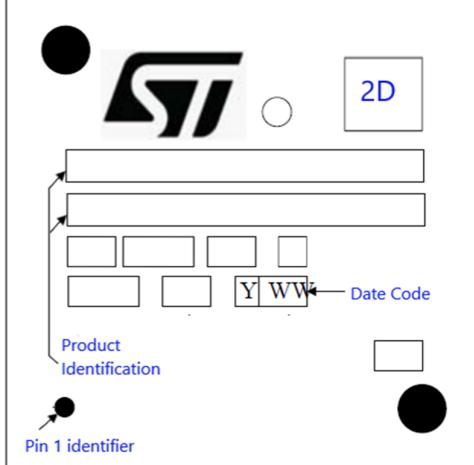
Changes described in table below:

	Existing back-end line	Added back-end line
Assembly site	ASE KaoHsiung (Taiwan)	
Wire	Gold 0.8mil	CuPdAu 0.8mil
GLUE	SUMITOMO CRM 1076WA	HITACHI EN4900G
Marking composition	Without 2D	With 2D Marking

## How can the change be seen?

Package top view Marking will display the 2D marking

Examples in below table

	Existing line	Added Line
LQFP 24x24	 <p>Diagram illustrating the package marking for an LQFP 24x24 package. The marking area is divided into several sections: a top row of four squares, a middle row of four squares, a bottom row of four squares, and a central column of four squares. The bottom-left square of the central column is labeled 'Product Identification'. To the right of the central column is a square labeled 'Y WW' with an arrow pointing to it, labeled 'Date Code'. Below the central column is a square labeled 'Pin 1 identifier'. The ST logo is located at the bottom right of the marking area. There are also two black circular features on the left and right edges of the marking area.</p>	 <p>Diagram illustrating the package marking for an LQFP 24x24 package, showing the addition of a 2D marking. The marking area is identical to the 'Existing line' diagram, but includes a new '2D' label in a blue box in the top right corner. The ST logo is also present in the top right corner.</p>

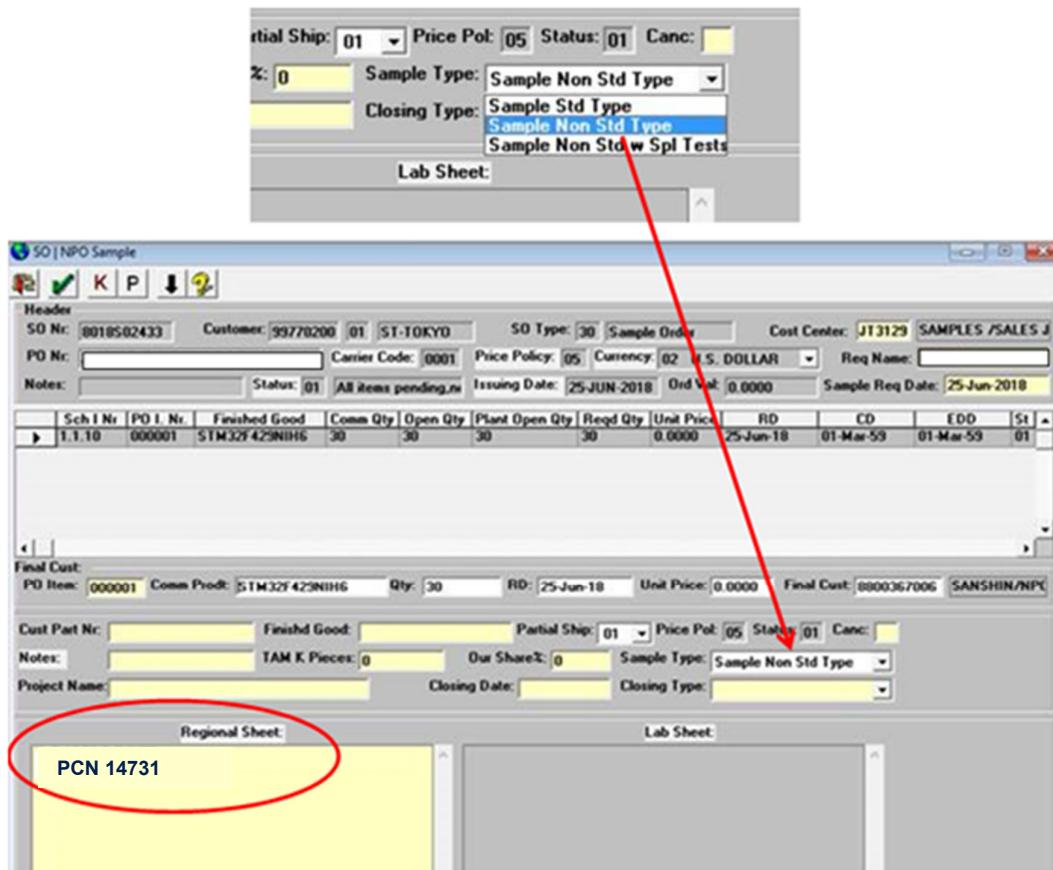
**Y WW** : Year Week (manufacturing date)

Please refer to product [DataSheet](#) or Technical Note **TN1433** for package marking details.

## How to order samples?

For all samples request linked to this PCN, please:

- place a **Non-standard** sample order (choose Sample Non Std Type from pull down menu).
- insert the PCN number “**PCN14731**” into the NPO Electronic Sheet/**Regional Sheet**.
- request sample(s) through Notice tool, indicating a single Commercial Product for each request.





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**PCN Title :** ASE KaoHsiung (Taiwan) LQFP24x24 package copper palladium bonding wire introduction on STM32H56x and STM32H57x on additional listed products.

**PCN Reference :** MICROCONTROLLERS/24/14731

**Subject :** Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

STM32H562IGT6	STM32H563IIT3Q	STM32H562IIT6
STM32H563IIT6	STM32H573IIT3Q	STM32H573IIT6
STM32H563IGT6		

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